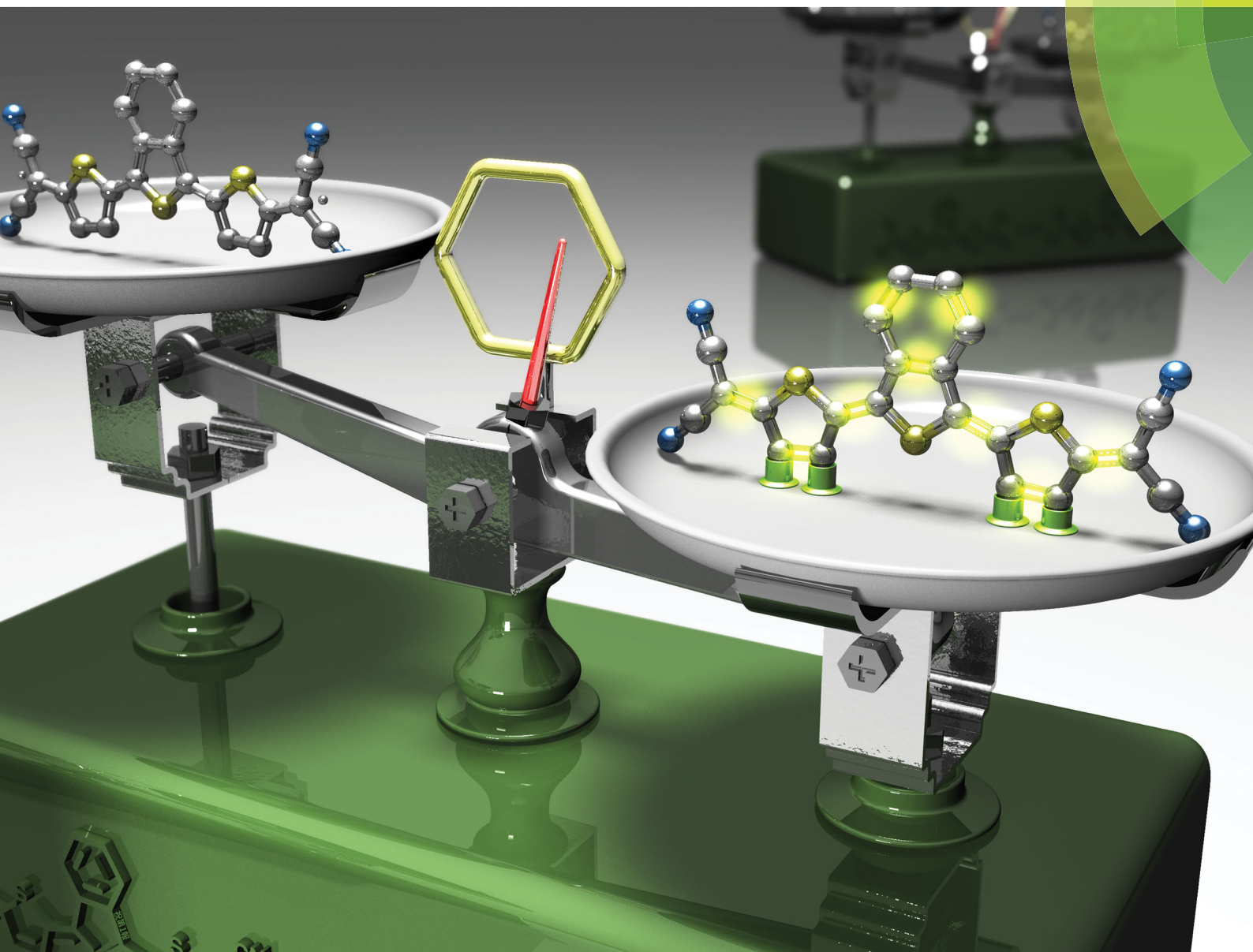


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Oligothiophene quinoids containing a benzo[*c*]thiophene unit for the stabilization of the quinoidal electronic structure

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Oligothiophene quinoids containing a benzo[*c*]thiophene unit for the stabilization of the quinoidal electronic structure†

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Bis(dicyanomethylene)-substituted quinoidal π -conjugated systems possess a high electron-accepting nature and thus have been extensively investigated for application as n-type semiconductors. We focus on the utilization of benzene-annulation for the stabilization of the quinoidal electronic structure against the biradicaloid structure by designing quinoidal thiophenes 3-mer (**BTQ**) and 6-mer (**BTQ-6**) that have benzo[*c*]thiophene units. We also develop quinoidal oligothiophenes (**BTQ-F**) consisting of both benzo[*c*]thiophene and fluorinated thiophene units. The influence of benzo[*c*]thiophene on the quinoidal electronic structure is investigated by theoretical studies and property measurements. The molecular structure of **BTQ-F** is unambiguously confirmed through single-crystal X-ray diffraction. Analyses of cyclic voltammetry reveal that the lowest unoccupied molecular orbital energy levels of these compounds lie below -4.0 eV, leading to good electron-transporting characteristics even under ambient conditions in organic field-effect transistors (OFETs). Due to an increased highest occupied molecular orbital energy level, ambipolar transport is observed in **BTQ-6**, indicating the versatility of quinoidal π -conjugated systems incorporating benzo[*c*]thiophene.

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Introduction

Significant research interest continues to be focussed on structurally well-defined π -conjugated oligomers, not only for the elucidation of fundamental structure–property relationship, but also for their applications in organic thin-film electronics such as organic field-effect transistors (OFETs) and organic photovoltaics.^{1,2} π -Conjugated compounds bearing quinoidal structures have

been extensively investigated not only as a model structure of doped conducting arylene polymers, but also as a Wurster-type multi-redox system in Hünig's classification.³ Among them, bis(dicyanomethylene)-substituted quinoidal compounds, which generate an anionic aromatic state by accepting one or two electrons, exhibit a high electron-accepting ability for instance the well-known compound tetracyano-*p*-quinodimethane.⁴ Therefore, the extension of the π -conjugation of such quinoidal systems, typically tetracyano quinoidal oligothiophenes, has attracted great attention for promising electron-transporting (n-type) semiconductors.^{5–13} Another unique feature of the quinoidal systems is the equilibrium between quinoidal and biradicaloid electronic structures,¹⁴ which causes a configurational instability of quinoidal oligothiophenes. A representative approach to increase the contribution of the quinoid character in oligothiophenes involves the utilization of aromatic stabilization in the quinoidal form, which was accomplished by the introduction of a fused aromatic ring on the thiophene [*c*]bond, as observed first in the synthesis of poly-(isothianaphthene) with a small band gap by Wudl *et al.*¹⁵ In this context, quinoidal oligothiophenes containing thieno[3,4-*b*]thiophene have been extensively developed by Zhu *et al.*¹⁶ We envisioned that if the benzo[*c*]thiophene (isothianaphthene) quinoid unit can be incorporated into π -extended quinoidal structures, the high aromatic stabilization energy of this unit

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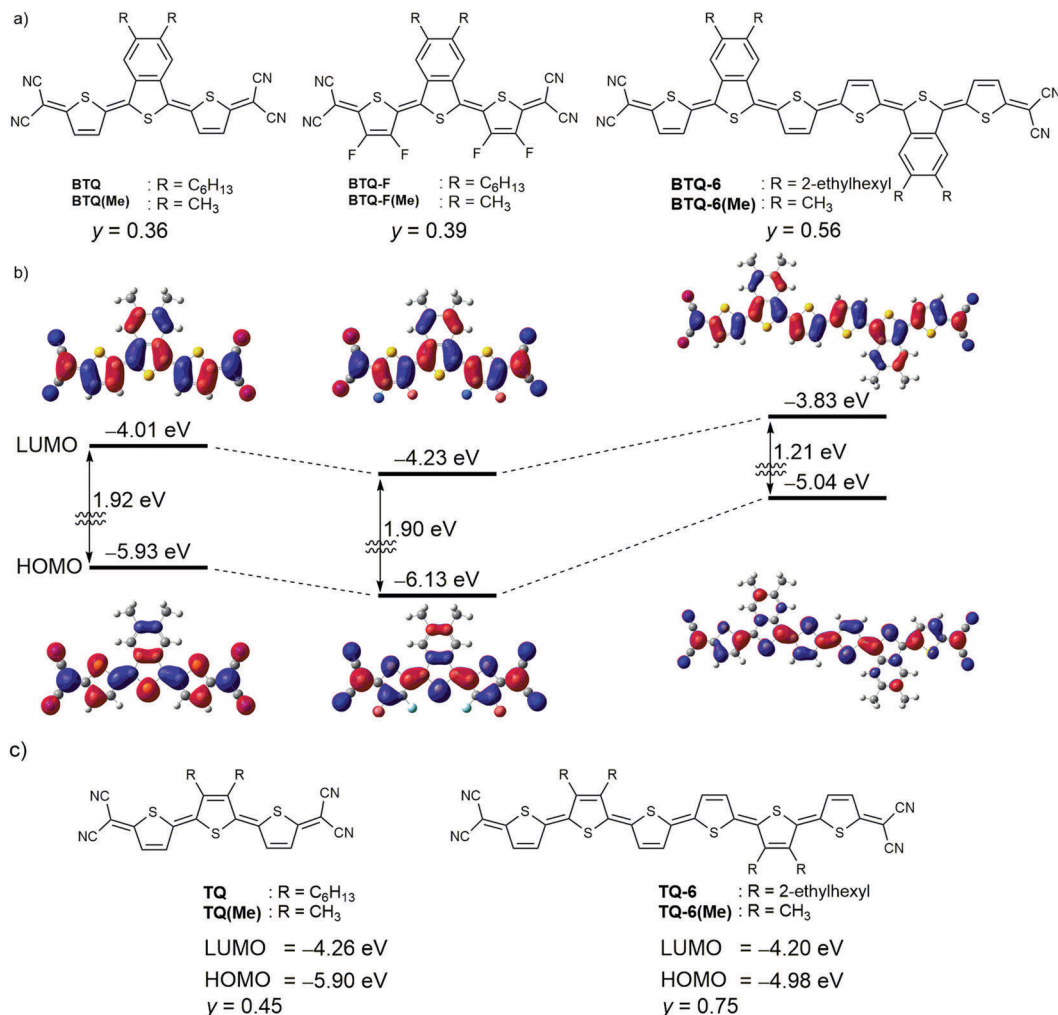


Fig. 1 (a) Chemical structures of compounds investigated in this study. (b) Calculated energy levels and orbitals for model compounds **BTQ(Me)** (left), **BTQ-F(Me)** (center), and **BTQ-6(Me)** (right). (c) Chemical structures of reference compounds.

compared to that of benzo[*c*]thiophene would allow us to create quinoidal oligothiophenes that have potential as air-stable semiconducting materials. To pursue this possibility, we designed new bis(dicyanomethylene)-substituted quinoidal oligothiophenes (**BTQ** and **BTQ-6**) containing 5,6-dialkylbenzo[*c*]thiophene units (Fig. 1). Furthermore, in order to increase the electron-accepting ability of **BTQ**, fluorine substituents were introduced at the β -position of the quinoidal terthiophene (**BTQ-F**). In this contribution, we report on the synthesis, properties, structures, and OFET characteristics of these compounds. Although the parent bis(dicyanomethylene)benzo[*c*]thiophene was synthesized and characterized by Cava *et al.* in 1993,¹⁷ its π -extended derivative has not been reported so far.

Results and discussion

Theoretical studies

To estimate the molecular structure and frontier orbital energies, we performed density functional theory (DFT) calculations at the

B3LYP/6-31G(d,p) level of theory. All alkyl groups were replaced with methyl groups for the ease of the calculation. Optimized geometries of **BTQ(Me)**, **BTQ-F(Me)**, and **BTQ-6(Me)** showed a planar conformation which indicates that the introduction of the benzene annelation in the central thiophene ring of terthiophene does not increase the distortion with respect to the dihedral angle (Fig. 1(b)). The lowest unoccupied molecular orbital (LUMO) energy level of **BTQ(Me)** is higher compared to that of **TQ(Me)** (Fig. 1(b) and (c)) but is still located at a low level of -4.01 eV. The substitution of hydrogen atoms in the thiophene rings with fluorine atoms for **BTQ-F(Me)** led to a further decrease of the LUMO energy level to -4.23 eV, while maintaining a similar highest occupied molecular orbital (HOMO)-LUMO energy gap. It should be mentioned that the LUMO of both compounds is delocalized over the entire π -conjugated backbone including the annelated benzene ring, which is favorable for the intermolecular overlap of LUMOs between neighboring molecules in the solid state.^{16b} On the other hand, the extension of π -conjugation from **BTQ(Me)** to **BTQ-6(Me)** mainly contributes to an increase of the HOMO energy level from -5.93 eV to -5.04 eV. The singlet



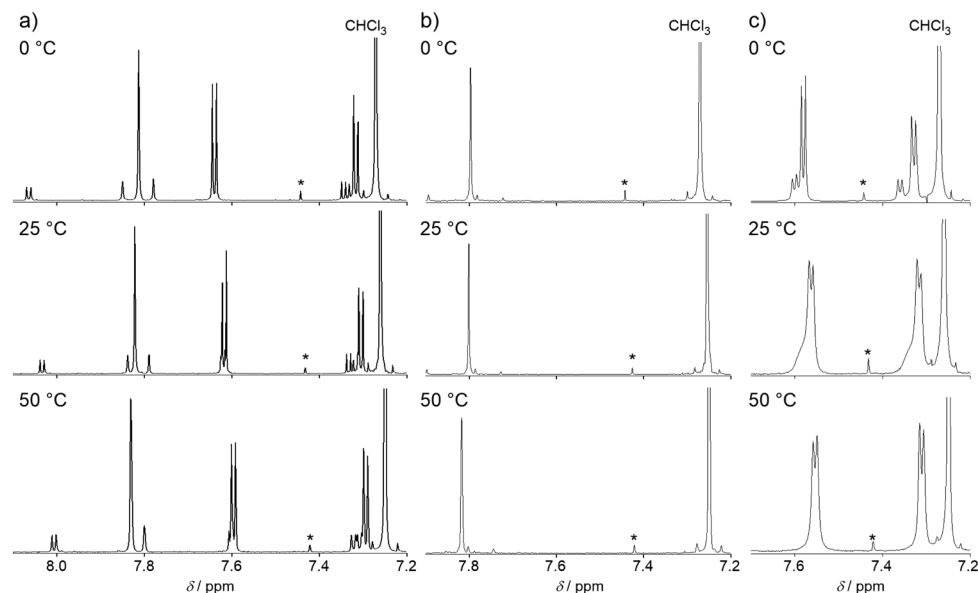


Fig. 2 VT-NMR spectra of (a) **BTQ**, (b) **BTQ-F**, and (c) **TQ** in the aromatic regions in CDCl_3 . Signals marked by an asterisk are satellite peaks in CHCl_3 .

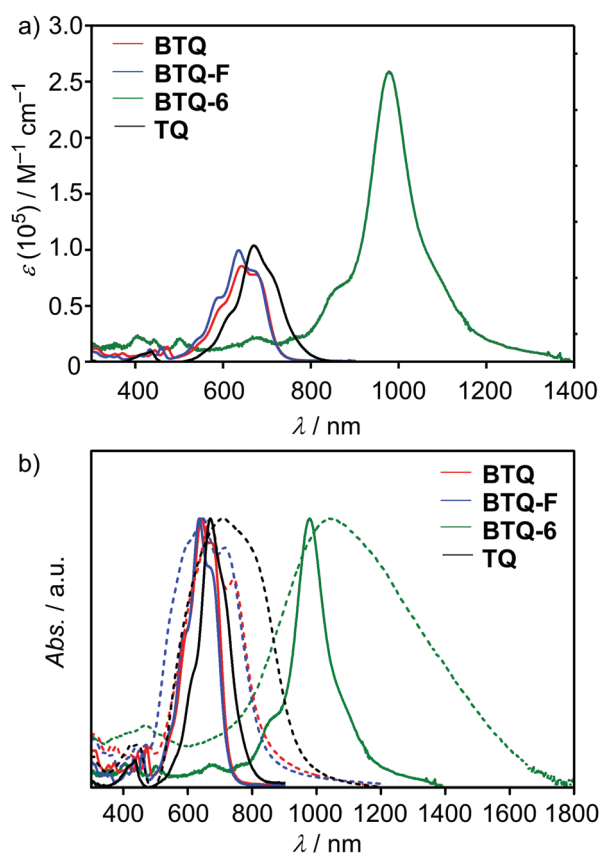


Fig. 3 (a) UV-vis-NIR absorption spectra of **BTQ** (red) and **BTQ-F** (blue), **TQ** (black), and **BTQ-6** (green) in CH_2Cl_2 and (b) in CH_2Cl_2 (solid line) and thin films (dashed line).

are found to be *ca.* 1.7 eV. The absorption spectrum of **BTQ-6** in CH_2Cl_2 solution exhibited an absorption band at the near-infrared region ($\lambda_{\text{max}} = 978 \text{ nm}$) with a large ϵ of $2.6 \times 10^5 \text{ M}^{-1} \text{ cm}^{-1}$.

Table 1 Photophysical and electrochemical properties

Compound	λ_{max}^a ($\epsilon \times 10^5$)/ nm ($\text{M}^{-1} \text{ cm}^{-1}$)	$\Delta E_{\text{g}}^{\text{opt}a}$ / eV	$E_{1/2}^{\text{ox}b}$ / V	$E_{1/2}^{\text{red}b}$ / V	E_{HOMO}^c / eV	E_{LUMO}^d / eV
BTQ	642 (0.9)	1.70	0.86	-0.74	-5.66	-4.06
BTQ-F	636 (1.0)	1.71	1.05	-0.50	-5.85	-4.30
BTQ-6	978 (2.6)	1.14	0.08	-0.54	-4.88	-4.26
TQ	670 (1.1)	1.60	0.81	-0.61	-5.61	-4.23

^a In CH_2Cl_2 . ^b In CH_2Cl_2 containing 0.1 M TBAPF₆. V vs. Fc/Fc⁺. ^c $E_{\text{HOMO}} = -E_{1/2}^{\text{ox}} - 4.8$. ^d $E_{\text{LUMO}} = -E_{1/2}^{\text{red}} - 4.8$.

This behavior is in contrast to a previous report where quinoidal sexithiophene showed a reduced molar extinction coefficient with concomitant appearance of marked absorptions in the visible region, compared to the corresponding quinoidal quinquethiophene. The reduced extinction coefficient was attributed to the high contribution of the biradical character,^{14b} which indicates that the high ϵ of **BTQ-6** is rationalized by the higher contribution of the quinoidal electronic structure owing to the presence of benzo[*c*]thiophene units in the framework. Compared to the solution spectra, well-structured shoulders with red-shifted λ_{max} were observed for **BTQ** and **BTQ-F** in thin films (Fig. 3(b)). This phenomenon is attributed to the intermolecular electronic interactions of π - π stacked backbones, which are favorable for carrier transport in thin-film devices. The absorption spectrum of **BTQ-6** in thin films showed a broad absorption with the onset reaching 1800 nm. Such a large bathochromic shift was observed for quinoidal quaterthiophene.⁹ In addition to the intermolecular electronic interactions, the existence of the biradical character may have influence on this bathochromic shift.

The electrochemical properties of these compounds were investigated by cyclic voltammetry (CV) measurements in CH_2Cl_2 containing 0.1 M tetrabutylammonium hexafluorophosphate (TBAPF₆) as the supporting electrolyte. All potentials are



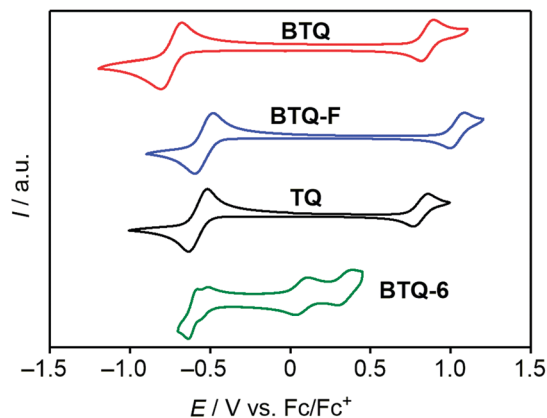


Fig. 4 Cyclic voltammograms of **BTQ** (red) and **BTQ-F** (blue), **TQ** (black), and **BTQ-6** (green) in CH_2Cl_2 containing 0.1 M TBAPF₆.

calibrated against a ferrocene/ferrocenium (Fc/Fc^+) couple as the standard, and these values are listed in Table 1. As presented in Fig. 4, the cyclic voltammograms of **BTQ**, **BTQ-F**, and **TQ** showed one reversible oxidation wave and a reduction wave. The observed good reversibility indicates the stable formation of both cationic and anionic species. Integration of each peak area for these compounds implied the participation of one electron and two electrons in oxidation and reduction processes, respectively. As shown in Table 1, due to the electron-withdrawing nature of fluorine atoms, both the half-wave oxidation potential ($E_{1/2}^{\text{ox}}$) and reduction potential ($E_{1/2}^{\text{red}}$) of **BTQ-F** are positively shifted compared to those of **BTQ**. Based on the assumption that the energy level of Fc/Fc^+ is -4.8 eV below the vacuum level,^{21–23} the LUMO energy levels (E_{LUMO}) of **BTQ** and **BTQ-F** were estimated to be -4.06 and -4.30 eV, respectively. These values are in good agreement with those estimated from the theoretical calculation. For **BTQ-6**, two reversible oxidation and reduction processes were observed. The E_{LUMO} and E_{HOMO} of **BTQ-6** estimated from the first $E_{1/2}^{\text{red}}$ and $E_{1/2}^{\text{ox}}$ were -4.26 and -4.88 eV, respectively, indicating that the extension of the quinoidal π -system leads to a significant increase of the HOMO energy level. This qualitative trend of HOMO and LUMO energy levels is also in good agreement with the theoretical estimation.

X-Ray single-crystal structures

The structure of **BTQ-F** was unambiguously determined using X-ray crystallographic analysis of the crystals that were grown by slow evaporation from a solution in ethyl acetate (EtOAc) and a MeOH mixed solvent. As shown in Fig. 5(a), the molecular structure of **BTQ-F** adopts all *anti* and planar conformations with dihedral angles of less than 2.7° . On the other hand, the distance of the intramolecular S–F contact (2.75 Å) is smaller than the sum of van der Waals radii of S and F atoms (3.27 Å), indicating the presence of nonbonding attractive interactions between these atoms. In the packing diagram, **BTQ-F** molecules are oriented in a face-to-face fashion with minimum intermolecular π – π distances of 3.55 Å and 3.42 Å (a and b in Fig. 5(b), respectively). On the basis of the calculation by the Amsterdam Density Functional program at the PW91/TZP level, the transfer

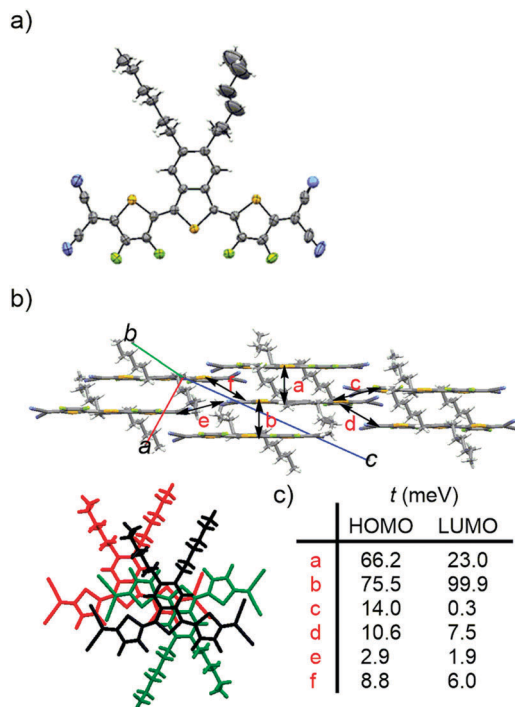


Fig. 5 (a) ORTEP drawing of the molecular structure, (b) packing diagram from side view (top) and top view (bottom), and (c) estimated packing transfer integrals of HOMOs and LUMOs for **BTQ-F**.

integrals between facial stacked structures of **BTQ-F** in the crystal were estimated. All the transfer integrals for electron transport (t_{LUMO}) and hole transport (t_{HOMO}) are shown in Fig. 5(c). **BTQ-F** showed a large t_{HOMO} and t_{LUMO} of 75.5 and 99.9 meV, respectively, which is expected to construct a charge-carrier transporting pathway along the stacking direction.

Charge carrier transport and film morphologies

To evaluate the semiconducting charge-transport characteristics of **BTQ**, **BTQ-F**, **BTQ-6**, and **TQ**, OFET devices based on thin films were fabricated. Although there have been several reports on high or finely tuned ambipolar OFETs of ter- and quaterthiophene quinoids,⁵ the compounds used in this work were characterized using a conventional bottom-gate bottom-contact transistor configuration with similar fabrication conditions for all devices. The active layer was prepared by spin-coating from a 0.3 wt% CHCl_3 solution onto hexamethyldisilazane (HMDS)-modified Si/SiO₂ substrates. Thermal annealing was effective for improving the performance for **BTQ** and **BTQ-F**, and the current-voltage characteristics of best-performance devices are shown in Fig. 6 and Fig. S3, S4 (ESI[†]). The hole (μ_{h}) and electron mobilities (μ_{e}) were extracted from the transfer characteristics at constant source-drain voltages. The corresponding device parameters such as mobility, threshold voltage (V_{th}), and current on/off ratio ($I_{\text{on}}/I_{\text{off}}$) are summarized in Table 2. Both **BTQ** and **BTQ-F** revealed solely an electron transport with μ_{e} in the order of 10^{-3} $\text{cm}^2 \text{V}^{-1} \text{s}^{-1}$ due to their low-lying LUMO energy levels. Furthermore, OFETs based on these compounds retained the same order of μ_{e} under air-exposed conditions. While the **TQ**-based device exhibited a higher



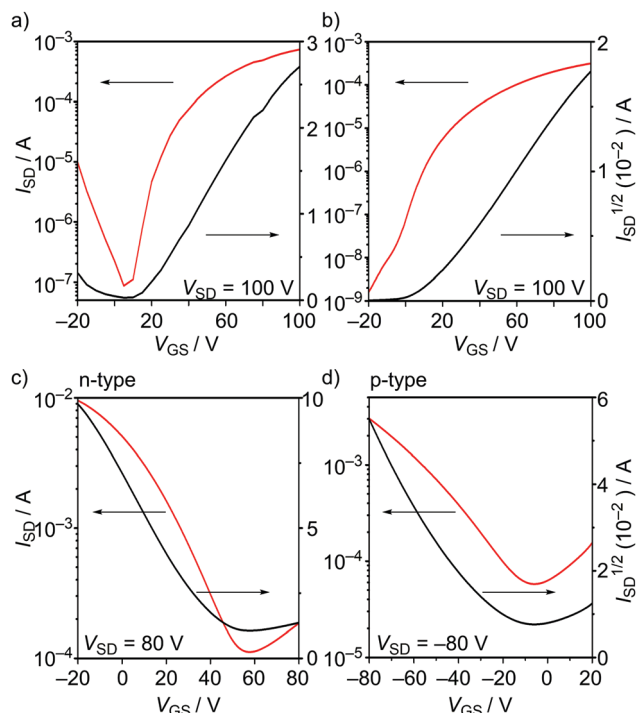


Fig. 6 (a) Transfer characteristics of OFETs using (a) **BTQ**, (b) **BTQ-F**, (c) **BTQ-6**, and (d) **BTQ-6**. V_{GS} , I_{SD} , and V_{SD} denotes gate voltage, source–drain current, and source–drain voltage, respectively.

Table 2 Field-effect characteristics under vacuum and in air

Compounds	Anneal temp./°C	V_{th}/V	I_{on}/I_{off}	$\mu_e/cm^2 V^{-1} s^{-1}$ ($\mu_{th}/cm^2 V^{-1} s^{-1}$)
BTQ ^a	170	15	10^4	3.4×10^{-3}
BTQ ^b	170	18	10^5	2.5×10^{-3}
BTQ-F ^a	170	13	10^5	1.2×10^{-3}
BTQ-F ^b	170	−9.4	10^3	3.0×10^{-4}
TQ ^a	As cast	35	10^1	3.3×10^{-2}
TQ ^b	150	22	10^2	3.4×10^{-2}
BTQ-6	As cast	78	10^1	8.9×10^{-4}
	(As cast) ^c	(−29) ^c	(10^2) ^c	(3.1×10^{-2}) ^c

^a Under vacuum. ^b In air. ^c Hole-transporting characteristics are shown in parenthesis.

μ_e compared with **BTQ** and **BTQ-F**, the I_{on}/I_{off} ratio was quite low due to a high off source–drain current (Fig. S4(d), ESI[†]). This might indicate that the ambipolar character of the **TQ** framework affects the increase of carrier density even in the off state.^{6b}

In order to investigate the film properties of these compounds, X-ray diffraction (XRD) and atomic force microscopy (AFM) measurements of these thin films on HMDS-modified Si/SiO₂ substrates were performed. As shown in Fig. 7 and Fig. S5 (ESI[†]), these compounds exhibited clear diffraction peaks in X-ray diffractogram (XRD), indicating the formation of crystalline structures in thin films. The peak of **BTQ-F** at $2\theta = 6.2^\circ$ can be indexed as the (011) diffraction peak with a d spacing of 14.2 Å according to the above-mentioned X-ray crystal structure analysis. Thus, the **BTQ-F** molecules are edge-on arranged with the stacking direction parallel to the SiO₂ surface. While the AFM image of **BTQ** revealed crystal-shaped

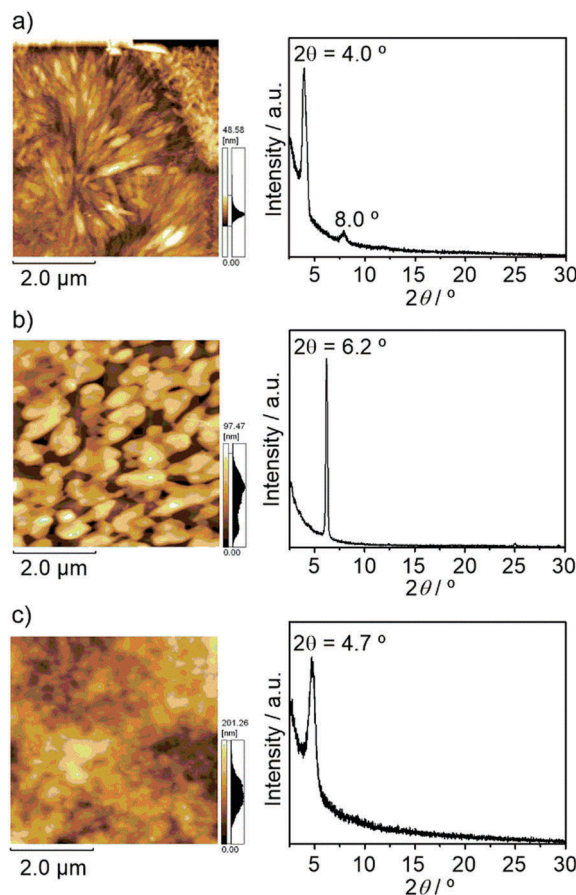


Fig. 7 AFM height images and XRD data of (a) **BTQ**, (b) **BTQ-F**, and (c) **BTQ-6**.

micrometer-sized grains, **BTQ-F** showed a rough film surface with large crystal grains (Fig. 7). Both **BTQ** and **BTQ-F** maintained OFET responses under air-exposed conditions, irrespective of the difference of the film morphologies. This result indicates that the observed air-stability mainly originates from the thermodynamic stability, *i.e.*, a low LUMO energy level of less than −4.0 eV. As discussed above, the introduction of benzene annelation led to the isomerization behavior different from that of **TQ** against temperature change. Therefore, to investigate the influence of the benzene annelation on the device characteristics, temperature-dependent OFET measurements of **BTQ**- and **TQ**-based devices were performed. For these measurements, we performed the surface modification of the source and drain gold electrodes using hexadecanethiol to minimize the contact resistance between Au electrodes and active layer.²⁴ The decreased contact resistance was confirmed by the output characteristics (Fig. S6, ESI[†]).

As shown in Fig. 8(a), OFETs using **BTQ** showed a decrease of electron mobility with decreasing temperature. This phenomenon is in agreement with the temperature dependence of hopping dominated carrier transport.²⁵ The activation energy of **BTQ** was estimated to be 0.13 eV (Fig. S7, ESI[†]). On the other hand, the **TQ**-based device showed a reverse trend with a decrease in the off current (Fig. 8(b)). We speculate that the diminution of the biradical character for **BTQ** might facilitate the inherent



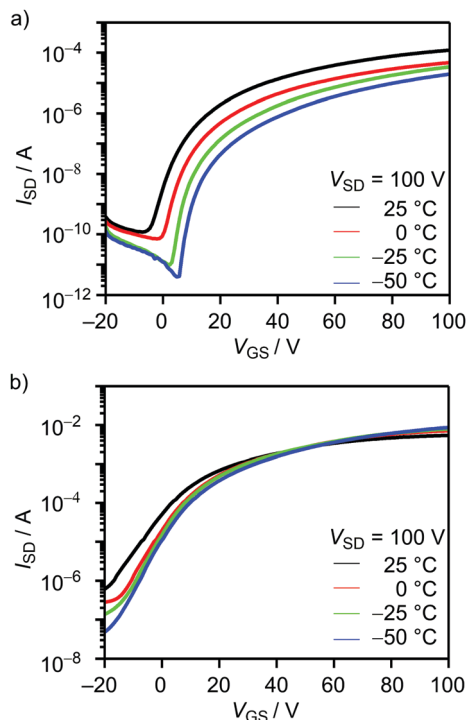


Fig. 8 Temperature-dependent transfer characteristics of the 1-hexadecanethiol-treated OFETs using (a) BTQ and (b) TQ.

electron transport, which means that biradicals act as carriers. Although the presence of the sterically bulky 2-ethylhexyl groups may prevent dense π - π stacking, XRD results indicate the crystalline structures in thin films (Fig. 7(c)). In fact, OFET devices based on BTQ-6 showed not only electron-transporting characteristics ($8.9 \times 10^{-4} \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$) but also hole-transporting characteristics ($3.1 \times 10^{-2} \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$). The appearance of p-type behavior can be explained by the increased HOMO energy levels. Note that the field-effect response for the quinoidal thiophene 6-mer is not reported so far. The OFET devices based on BTQ, TQ, and BTQ-6 were stored and measured periodically under the air-exposed conditions. As shown in Fig. S8 (ESI[†]), compared to TQ, a decrease of carrier mobility is suppressed for benzo[c]thiophene-containing semiconductors. We have considered that the introduction of the benzene annelation to form a stabilized quinoidal electronic structure becomes an effective strategy in developing new semiconducting materials.

Conclusions

In summary, to investigate the influence of benzene-annelation on the stabilization of the quinoidal electronic structure, we successfully synthesized new bis(dicyanomethylene)-substituted quinoidal oligothiophenes containing benzo[c]thiophene units. We also developed quinoidal oligothiophenes containing both a benzo[c]thiophene unit and fluorinated thiophenes. Theoretical calculations as well as experimental results indicate that the introduction of benzo[c]thiophene into the oligothiophene π -conjugated quinoid system is effective in stabilizing quinoidal

electronic structures. These molecules showed good electron-transporting characteristics, and the extension of π -conjugation from thiophene 3-mer to 6-mer led to the appearance of both hole- and electron-transporting characteristics. These results show that quinoidal π -conjugated systems containing benzo[c]thiophene units show potential as candidates for semiconducting materials using stabilized quinoidal structures. Further investigations toward expansion of the π -conjugation are currently underway in our group.

Conflicts of interest

There are no conflicts to declare.

Acknowledgements

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